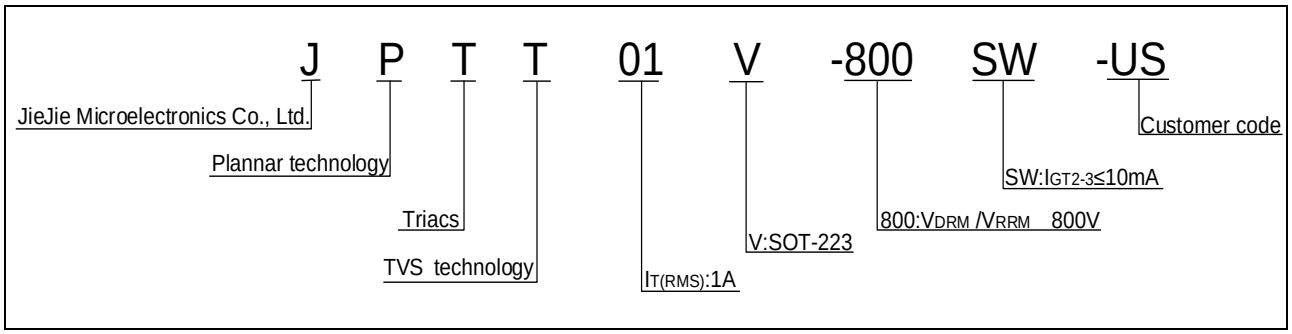
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	2	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.8)	V_{pp}	2.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	-	MAX.	10	mA
V_{GT}		-	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3KΩ	-	MIN.	0.15	V
I_L	I_G =1.2I_{GT}		MAX.	40	mA
				20	
I_H	I_T =100mA		MAX.	20	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	1000	V/μs
(dI/dt)c	(dV/dt)c=15V/μs, T_j=125		MIN.	2	A/ms
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25		TYP.	2.5	μs
t_{off}				25	
V_{CL}	I_{CL}=0.1mA t_p=1ms		MIN.	950	V

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =1.1A t_p=380μs	T_j=25	1.35	V
V_{TO}	Threshold voltage	T_j=125	0.8	V
R_D	Dynamic resistance	T_j=125	385	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	2	mA
I_{RRM}		T_j=125	0.2	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	25	/W
$R_{th(j-a)}$	junction to ambient (AC)	150	/W


J P T T 01 V -800 SW -US
JieJie Microelectronics Co., Ltd.
Plannar technology
Triacs
TVS technology
IT(RMS):1A
V:SOT-223
800:VDRM /VRRM 800V
SW:IGT2-3≤10mA
Customer code

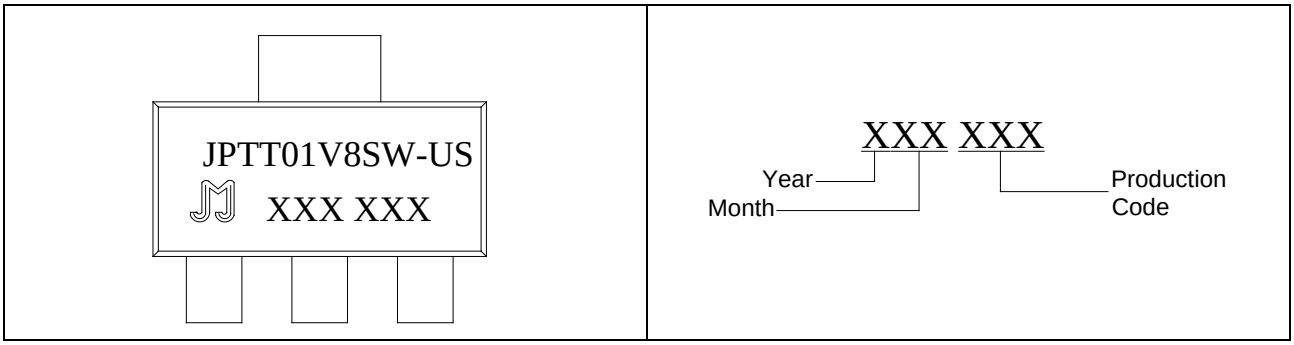

JPTT01V8SW-US
XXX XXX
XXX XXX
Year
Month
Production
Code

FIG.1 Maximum power dissipation versus RMS on-state current

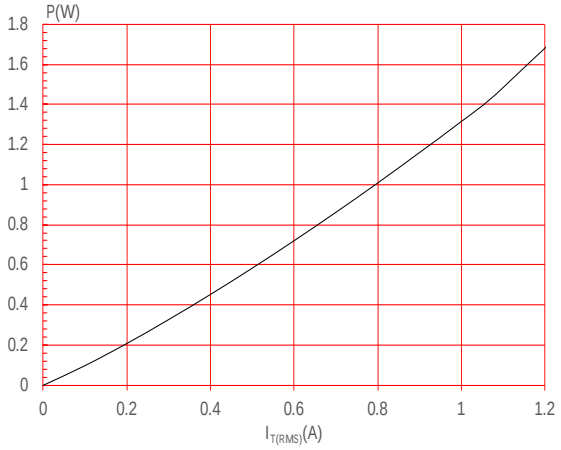


FIG.2: RMS on-state current versus case temperature

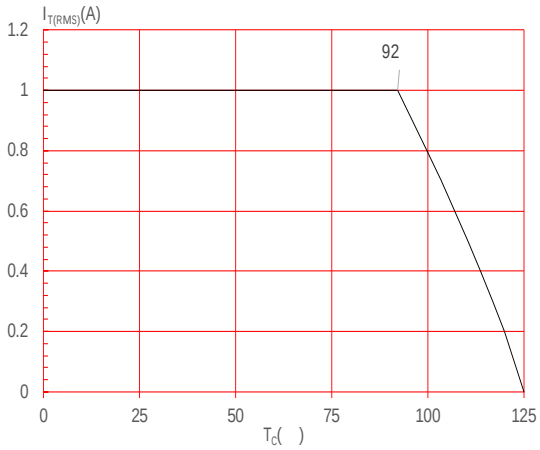


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

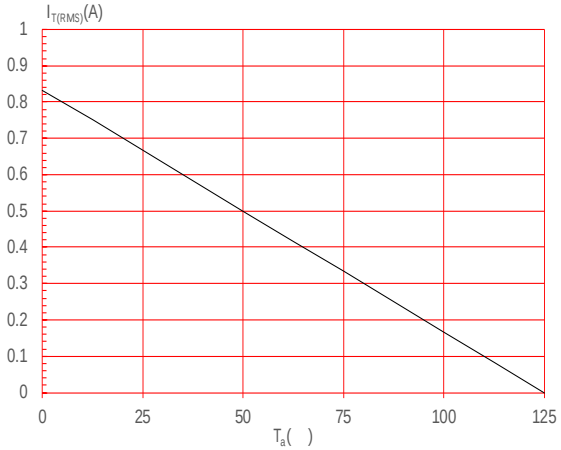
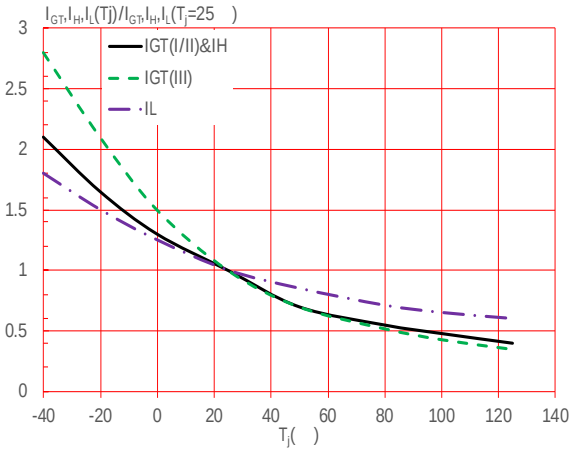


FIG.4: Surge peak on-state current versus number of cycles



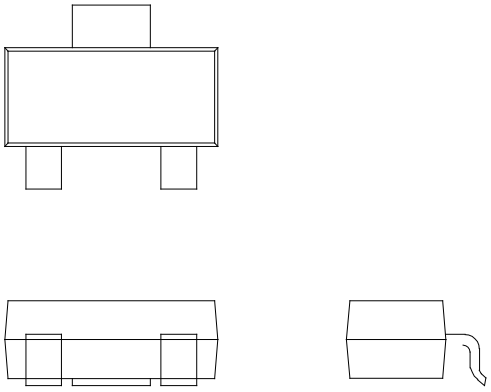
FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



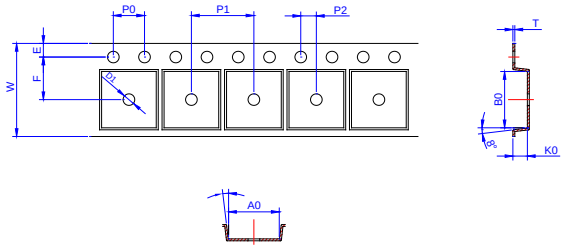
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JPTT01V-800SW-US	**800**	**10**	**SOT-223**	**4,000**	**Tape & Reel**

Document Revision History

Date	Revision	Changes
May.15, 2023	A-1	Last updated



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F	4.4			0.173		
F1	2.2			0.087		
G	0.5		1.0	0.020		0.039
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K		0.9			0.035	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-		12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0		1.55	1.60		0.061	0.063
D1		-	-			
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

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